

Silicon PNP Power Transistors

2SB548

DESCRIPTION

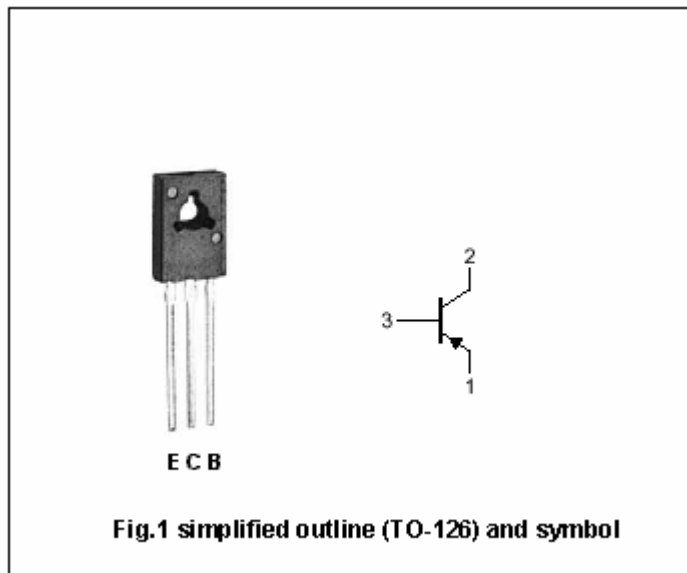
- With TO-126 package
- Complement to type 2SD414

APPLICATIONS

- Designed for use in driver and output stages of audio frequency amplifiers

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-0.8	A
P_D	Total power dissipation	$T_a=25^\circ\text{C}$	1.0	W
		$T_C=25^\circ\text{C}$	10	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-10mA ; I_B=0$	-80			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-50\mu A ; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-0.5A ; I_B=-50mA$			-2.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-0.5A ; I_B=-50mA$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-80V ; I_E=0$			-1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V ; I_C=0$			-1.0	μA
h_{FE}	DC current gain	$I_C=-0.2A ; V_{CE}=-5V$	40		320	
C_{OB}	Output capacitance	$I_E=0 ; V_{CB}=-10V ; f=1MHz$		25		pF
f_T	Transition frequency	$I_C=-0.1A ; V_{CE}=-5V$		70		MHz

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PACKAGE OUTLINE

